

Amendments to the Claims:

Please cancel Claims 1-13.

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-13 (canceled)

Claim 14 (original): A transistor formed at a semiconductor surface of a substrate, comprising:

a gate electrode extending along the surface for a length, the gate electrode having at least one second section disposed between adjacent ones of the first sections of the gate electrode, the at least one second section having a width that is narrower than the width of the adjacent ones of the first sections of the gate electrode; and

source and drain doped regions in the surface, and disposed on opposing sides of the gate electrode;

wherein the gate electrode is formed by a process comprising the steps of:

forming a conductive layer over the surface;

applying a layer of photosensitive masking material over the conductive layer;

exposing the photosensitive masking material to light through a photomask having an elongated feature, the feature having a plurality of first sections along its length of a width at or greater than a critical photolithographic dimension, and having at least one second section disposed between adjacent ones of the first sections of the feature, the at least one second section having a width less than the critical photolithographic dimension, the first sections and at least one second section of the feature defining the first sections and at least one second section of the gate electrode;

after the exposing step, removing the photosensitive masking material from locations not corresponding to the location of the gate electrode; and etching the conductive layer to form the gate electrode.

Claim 15 (original): The transistor of claim 14, wherein the critical photolithographic dimension corresponds to a minimum line width that may be defined by the exposing and removing of the photosensitive masking material.

Claim 16 (original): The transistor of claim 14, wherein the conductive material comprises polysilicon.

Claim 17 (original): The transistor of claim 14, wherein each of the plurality of first sections extends for a selected length along the feature;

and wherein the at least one second section extends for a length along the feature that is less than about three times the selected length of the plurality of first sections.

Claim 18 (original): The transistor of claim 14, wherein the at least one second section and its adjacent ones of the plurality of first sections have sides that are substantially parallel to the length of the elongated feature;

and wherein the elongated feature has edges, between the at least one second section and its adjacent ones of the plurality of first sections, that are substantially perpendicular to the sides of the at least one second section and its adjacent ones of the plurality of first sections.

Claim 19 (original): The transistor of claim 18, wherein the elongated feature has a side that defines substantially a straight line segment.

Claim 20 (original): The transistor of claim 14, wherein the at least one second section and its adjacent ones of the plurality of first sections have sides that are substantially parallel to the length of the elongated feature;

wherein the sides of the at least one second section and its adjacent ones of the plurality of first sections are separated by sloping portions of the elongated feature.

Claim 21 (original): The transistor of claim 14, wherein the elongated feature has a side that defines substantially a straight line segment.

Claim 22 (original): The transistor of claim 14, wherein the at least one second section and its adjacent ones of the plurality of first sections have sides that are substantially parallel to the length of the elongated feature;

and wherein opposing sides of the at least one second section and its adjacent ones of the plurality of first sections are substantially aligned with one another.

Claim 23 (original): The transistor of claim 14, wherein the at least one second section and its adjacent ones of the plurality of first sections have sides that are substantially parallel to the length of the elongated feature;

and wherein opposing sides of the at least one second section and its adjacent ones of the plurality of first sections are staggered relative to one another.